

N-channel 40 V, 2.4 mΩ logic level MOSFET in LFPAK56 4 June 2018

Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in • same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS •
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - · High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced Rth and RDSon
 - Increases maximum current capability and improved current spreading •

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	163	W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static chara	acteristics		· · ·		·		
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10		1.35	1.93	2.4	mΩ
Dynamic ch	naracteristics				•		_
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 20 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13		-	5.9	11.7	nC
Source-dra	in diode						
Q _r	recovered charge	I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	24.9	-	nC
S	softness factor	V _{DS} = 20 V		-	0.85	-	

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source	mb	D			
2	S	source					
3	S	source	a	G C C			
4	G	gate		mbb076 S			
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)				

6. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
BUK9Y2R4-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y2R4-40H	92H440

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

BUK9Y2R4-40H

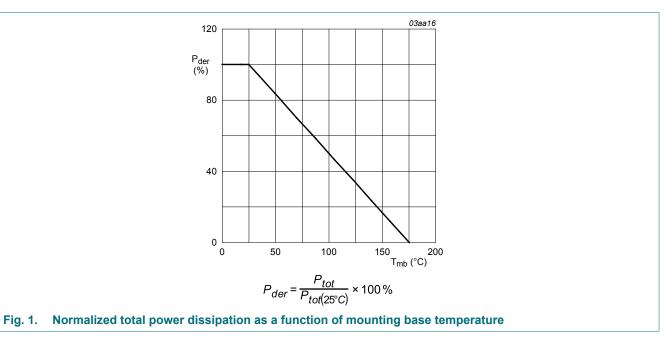
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Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	16	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	163	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 2		-	600	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C		-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness			-		-
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} {\sf I}_D = 120 \; {\sf A}; \; {\sf V}_{sup} \leq \; 40 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; ^{\circ}{\rm C}; \; \underline{{\sf Fig. 3}}; \\ {\sf unclamped} \end{array} $	[2] [3]	-	81.5	mJ

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

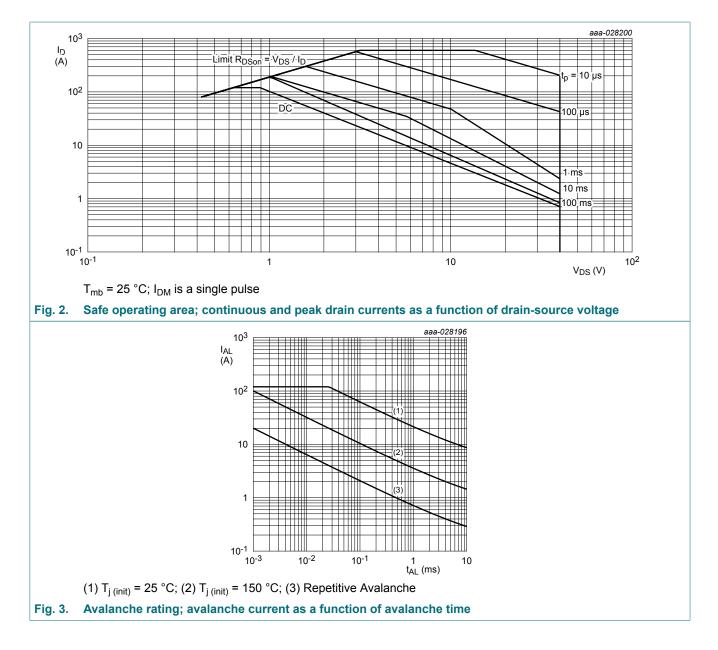
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



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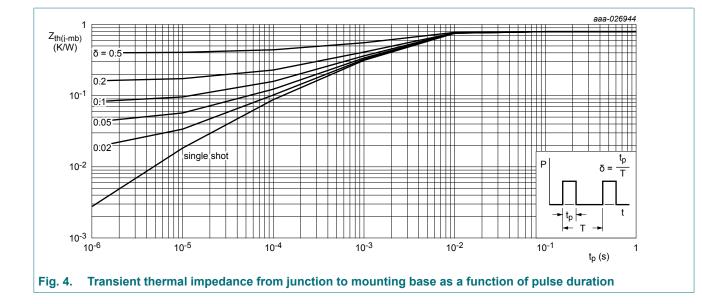
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.63	0.79	K/W

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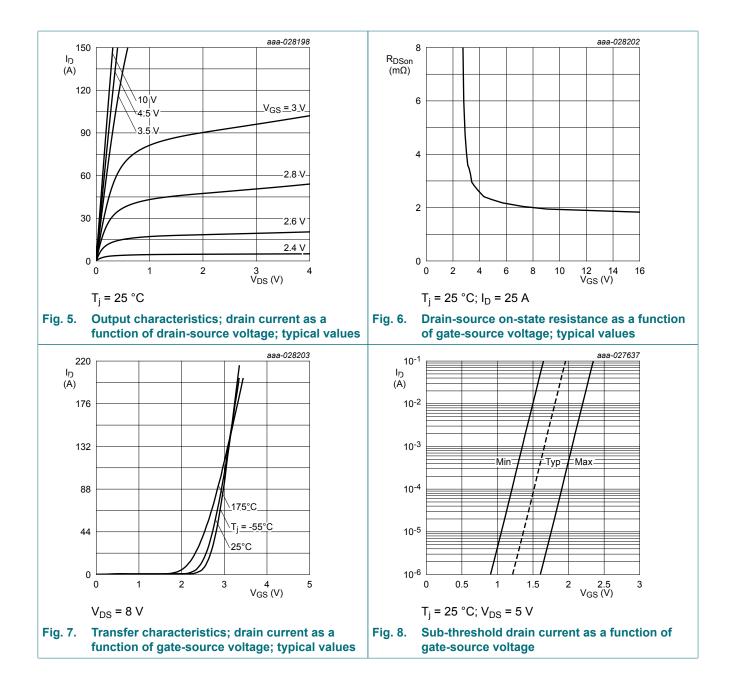
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·		-		_
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; <u>Fig. 8</u> ; Fig. 9	1.35	1.66	2.05	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.6	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.06	5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	1.2	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	142	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA

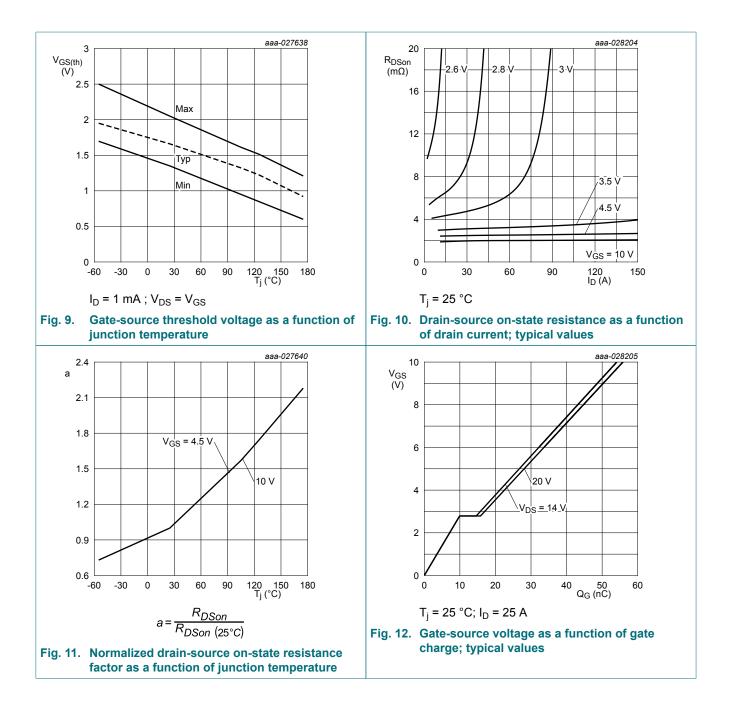
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	1.35	1.93	2.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; <u>Fig. 11</u>	2	2.95	3.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; <u>Fig. 11</u>	2.2	3.2	4.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; <u>Fig. 11</u>	2.8	4.11	5.2	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.68	2.4	3.2	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 105 °C; Fig. 11	2.5	3.67	5	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.8	4	5.7	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; Fig. 11	3.5	5.11	7	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.29	0.72	1.8	Ω
Dynamic ch	naracteristics	· · · · ·	I			_
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	55.8	78.2	nC
		I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	25.3	35.4	nC
Q _{GS}	gate-source charge		-	9.9	14.9	nC
Q _{GD}	gate-drain charge		-	5.9	11.7	nC
C _{iss}	input capacitance	<u>Fig. 12; Fig. 13</u> V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	3960	5544	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	859	1203	pF
C _{rss}	reverse transfer capacitance		-	140	308	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 0.8 Ω; V _{GS} = 4.5 V;	-	23.1	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	26.3	-	ns
t _{d(off)}	turn-off delay time		-	27.2	-	ns
t _f	fall time		-	16.4	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	31	-	ns
Q _r	recovered charge	V _{DS} = 20 V	-	24.9	-	nC
S	softness factor	1 1	-	0.85	-	
		I_{S} = 25 A; dI _S /dt = -500 A/µs; V _{GS} = 0 V; V _{DS} = 20 V	-	0.67	-	

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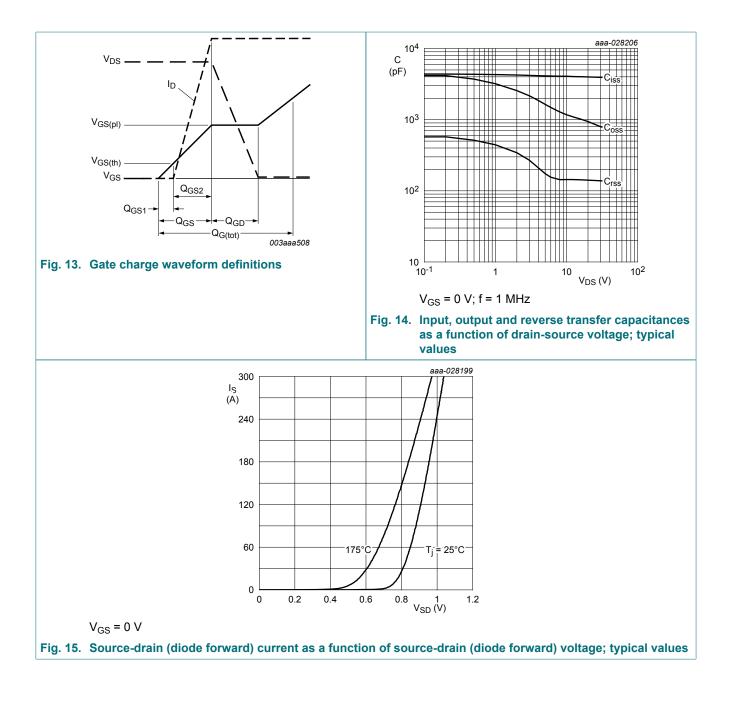


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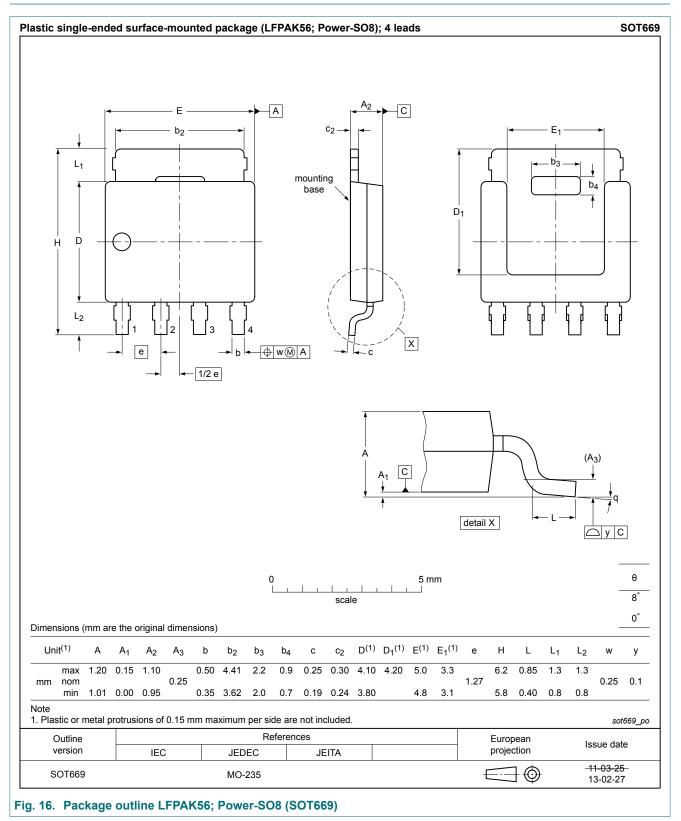
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11. Package outline



BUK9Y2R4-40H

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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